

## **isc** Silicon NPN Power Transistor

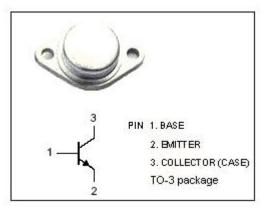
## 2SC2123

#### DESCRIPTION

- · High Collector-Base Breakdown Voltage-
  - : V<sub>(BR)CBO</sub>= 1000V (Min)
- High Current Capability
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for TV horizontal output and high power switching applications.



#### F D 2PL -Q-G в -Qmm MIN MAX DIM 39.00 A 25.30 26.67 В 7.80 8.50 C D 0.90 1.10 E 1.60 1.40 10.92 G 5.46 Н \_ 11.30 κ 13.50 16.75 17.05 19.40 19.62 N 0 4.00 4.20 30.20 30.00 U ٧ 4.30 4.50

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	МАХ	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	1000	V	
Vceo	Collector-Emitter Voltage	400	V	
V <sub>EBO</sub>	Emitter-Base Voltage	8	V	
lc	Collector Current-Continuous	12	А	
Ісм	Collector Current-Peak	15	A	
Pc	Collector Power Dissipation @Tc=25°C	50	W	
Tj	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C	

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# 2SC2123

### **ELECTRICAL CHARACTERISTICS**

### $T_{\text{c}}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	400			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	1000			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	8			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= 8A; I <sub>B</sub> = 2.5A			3.3	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 2.5A			2.2	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1000V; I <sub>E</sub> = 0			1.0	mA
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		6		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 20V; f <sub>test</sub> = 1.0MHz		125		pF
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 8A; I <sub>B1</sub> = -I <sub>B2</sub> = 2.5A			1.0	μ <b>S</b>

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